

SI2315BDS-T1-E3-VB Datasheet

Trench Single-P -20V SOT23-3 MOSFET

PRODUCT SUMMARY

V_{DS} (V)	- 20
$R_{DS(on)}$ (Ω) at $V_{GS} = - 4.5$ V	0.034
$R_{DS(on)}$ (Ω) at $V_{GS} = - 2.5$ V	0.046
$R_{DS(on)}$ (Ω) at $V_{GS} = - 1.8$ V	0.067
I_D (A)	- 5
Configuration	Single

FEATURES

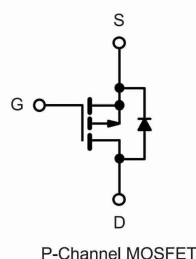
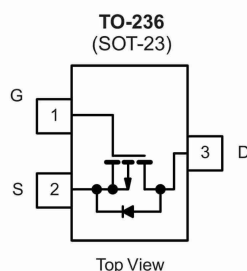
- Halogen-free Option Available
- TrenchFET® Power MOSFET

APPLICATIONS

- Load Switch for Portable Devices



RoHS
COMPLIANT
HALOGEN
FREE



ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	- 20	V
Gate-Source Voltage	V_{GS}	± 8	
Continuous Drain Current	I_D	$T_C = 25$ °C	A
		$T_C = 125$ °C	
Continuous Source Current (Diode Conduction)	I_S	- 2.5	
Pulsed Drain Current ^a	I_{DM}	- 20	
Single Pulse Avalanche Current	I_{AS}	- 11	
Single Pulse Avalanche Energy	E_{AS}	6	mJ
Maximum Power Dissipation ^a	P_D	$T_C = 25$ °C	W
		$T_C = 125$ °C	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 175	°C

THERMAL RESISTANCE RATINGS

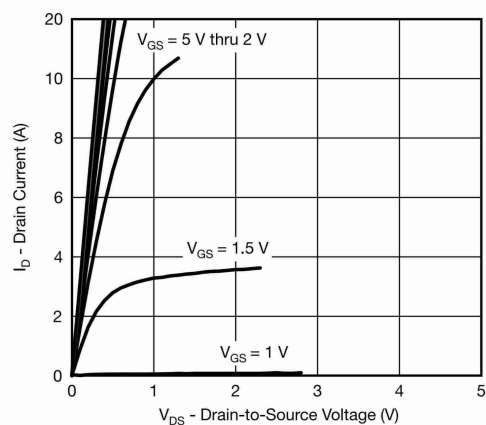
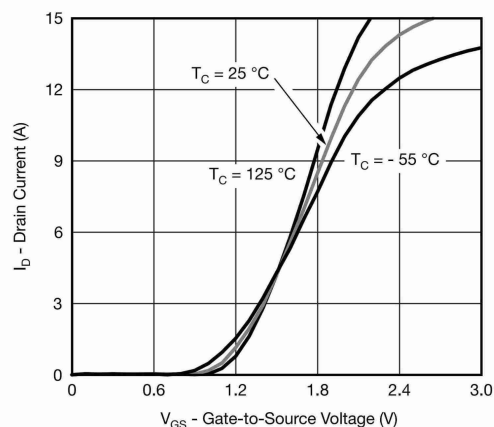
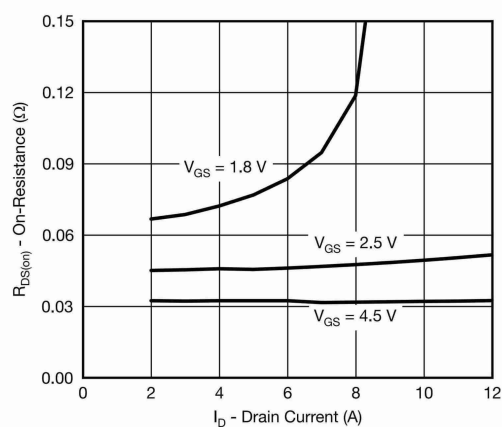
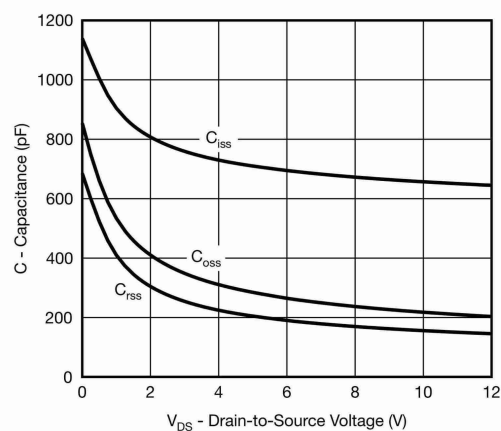
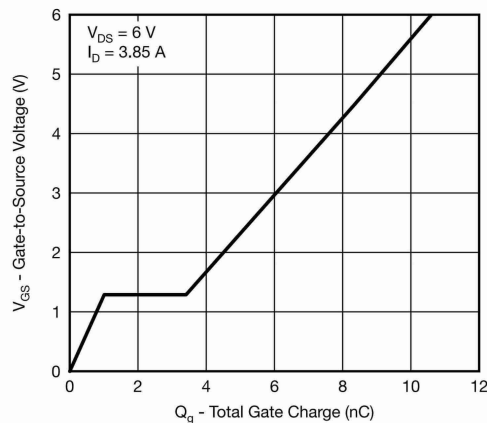
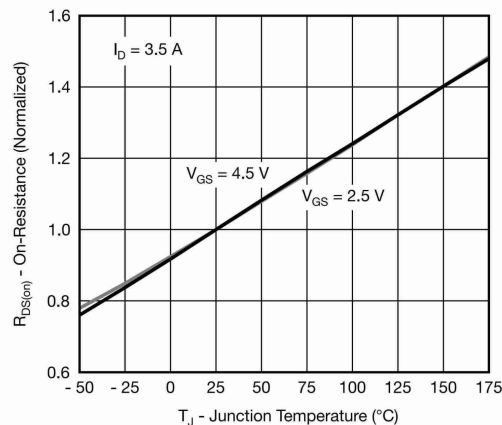
PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient	R_{thJA}	175	°C/W
Junction-to-Foot (Drain)	R_{thJF}	75	

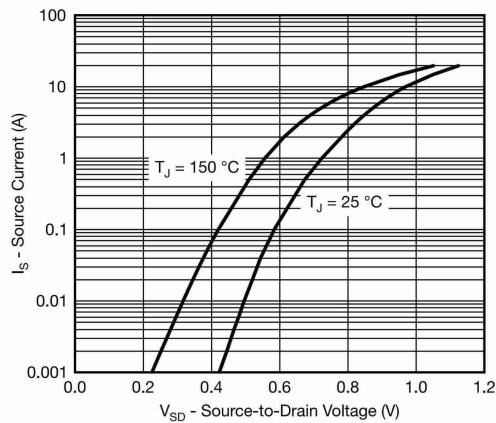
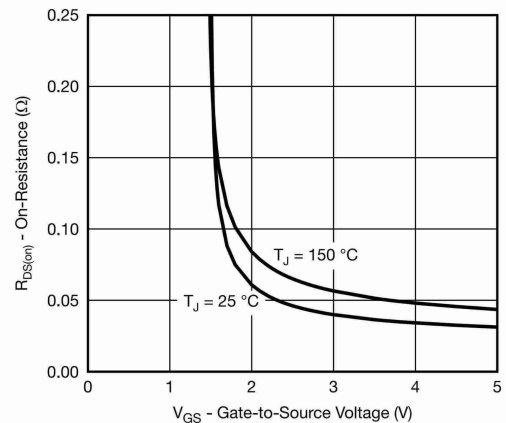
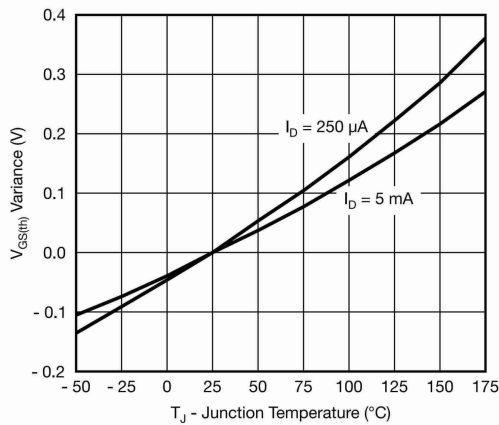
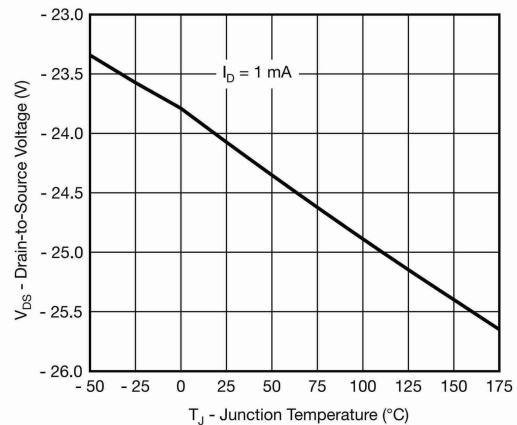
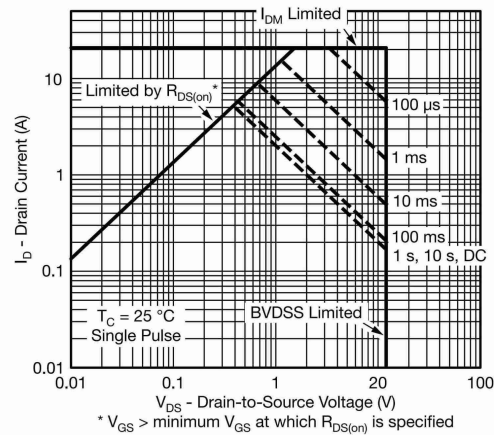
SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = - 250 μA	- 20	-	-	V	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 250 μA	- 0.45	-	- 1		
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 8 V	-	-	± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = - 12 V	-	-	- 1	μA
		V _{GS} = 0 V	V _{DS} = - 12 V, T _J = 125 °C	-	-	- 50	
		V _{GS} = 0 V	V _{DS} = - 12 V, T _J = 175 °C	-	-	- 150	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = - 4.5 V	V _{DS} ≤ - 5 V	- 10	-	-	A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 4.5 V	I _D = - 3.5 A	-	0.034	-	Ω
		V _{GS} = - 4.5 V	I _D = - 3.5 A, T _J = 125 °C	-	0.066	-	
		V _{GS} = - 4.5 V	I _D = - 3.5 A, T _J = 175 °C	-	0.075	-	
		V _{GS} = - 2.5 V	I _D = - 3 A	-	0.046	-	
		V _{GS} = - 1.8 V	I _D = - 2 A	-	0.067	-	
Forward Transconductance ^b	g _{fs}	V _{DS} = - 5 V, I _D = - 1.6 A		-	7	-	S
Dynamic ^b							
Input Capacitance	C _{iss}	V _{GS} = 0 V	V _{DS} = - 6 V, f = 1 MHz	-	695	870	pF
Output Capacitance	C _{oss}			-	265	335	
Reverse Transfer Capacitance	C _{rss}			-	190	240	
Total Gate Charge ^c	Q _g	V _{GS} = - 4.5 V	V _{DS} = - 6 V, I _D = - 3.85 A	-	8.4	13	nC
Gate-Source Charge ^c	Q _{gs}			-	1	-	
Gate-Drain Charge ^c	Q _{gd}			-	2.4	-	
Gate Resistance	R _g	f = 1 MHz		4.1	8.2	12.3	Ω
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = - 6 V, R _L = 1.6 Ω I _D ≅ - 3.85 A, V _{GEN} = - 4.5 V, R _g = 1 Ω		-	17	26	ns
Rise Time ^c	t _r			-	19	29	
Turn-Off Delay Time ^c	t _{d(off)}			-	28	42	
Fall Time ^c	t _f			-	13	20	
Source-Drain Diode Ratings and Characteristics ^b							
Pulsed Current ^a	I _{SM}			-	-	- 20	A
Forward Voltage	V _{SD}	I _F = - 2 A, V _{GS} = 0 V		-	- 0.8	- 1.2	V

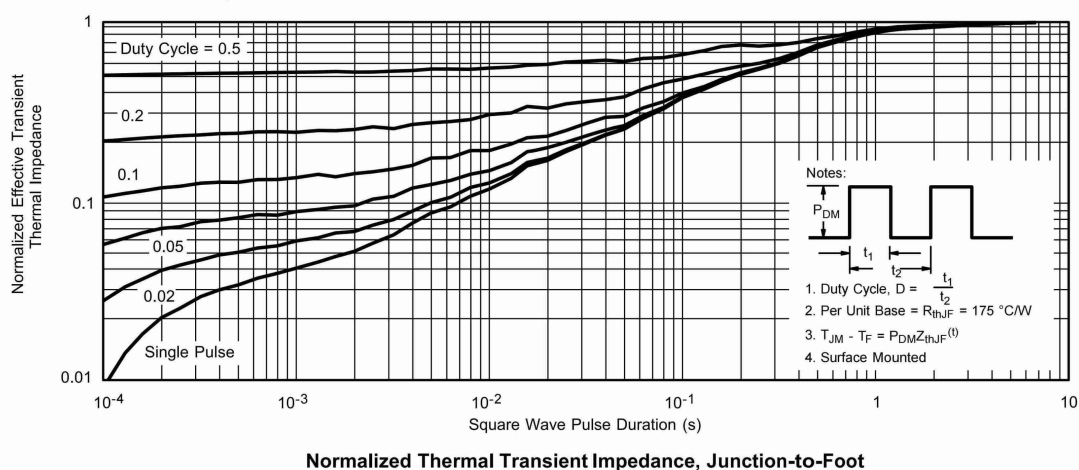
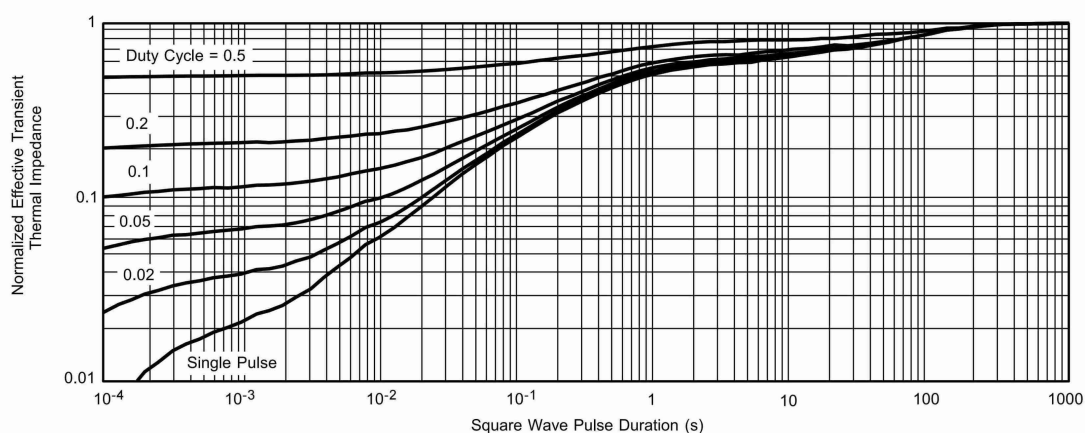
Notes

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
 b. Guaranteed by design, not subject to production testing.
 c. Independent of operating temperature.

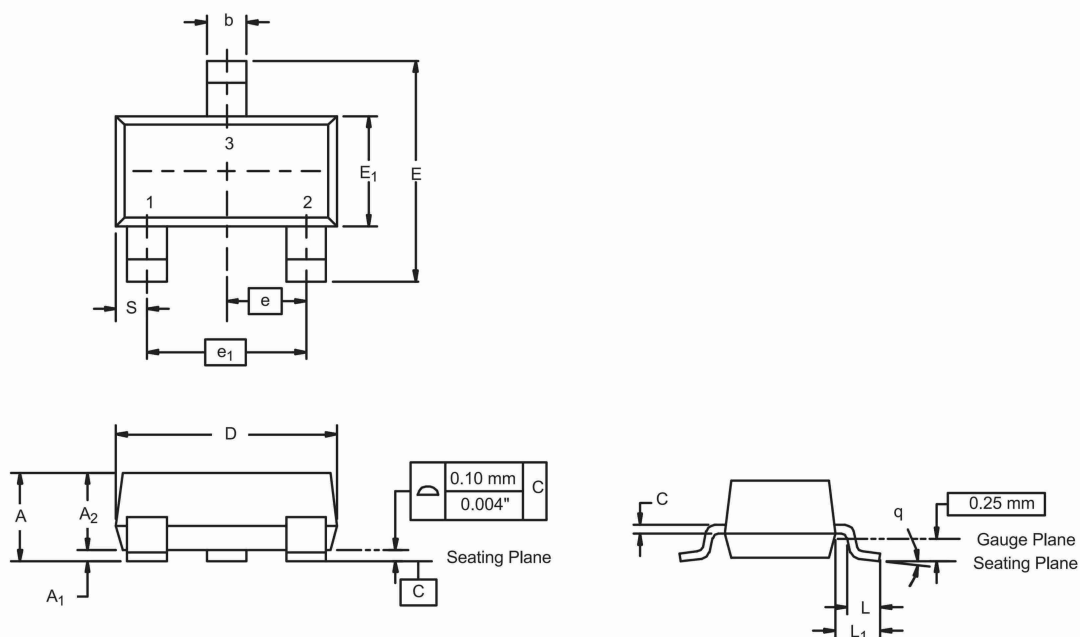
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise noted)

Output Characteristics

Transfer Characteristics

On-Resistance vs. Drain Current

Capacitance

Gate Charge

On-Resistance vs. Junction Temperature

TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)

Source-Drain Diode Forward Voltage

On-Resistance vs. Gate-to-Source Voltage

Threshold Voltage

Drain Source Breakdown vs. Junction Temperature

Safe Operating Area

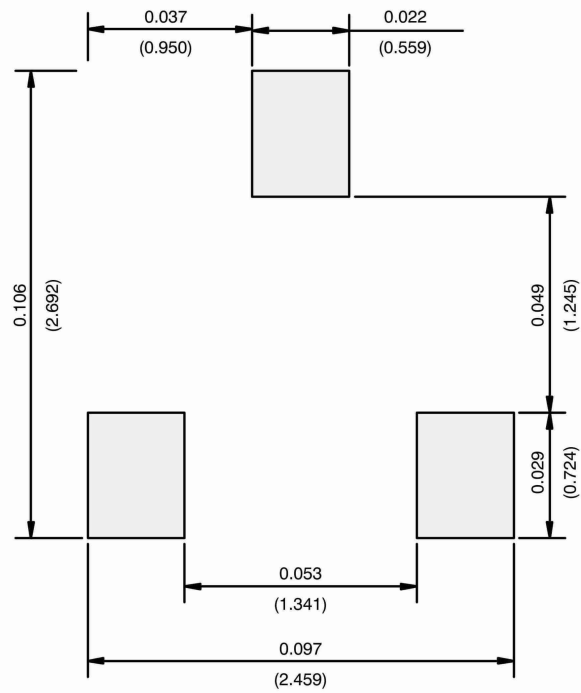
THERMAL RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Normalized Thermal Transient Impedance, Junction-to-Foot

Normalized Thermal Transient Impedance, Junction-to-Ambient
Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient ($25\text{ }^{\circ}\text{C}$)
 - Normalized Transient Thermal Impedance Junction-to-Foot ($25\text{ }^{\circ}\text{C}$)
 are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

SOT-23 (TO-236): 3-LEAD

Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	0.89	1.12	0.035	0.044
A ₁	0.01	0.10	0.0004	0.004
A ₂	0.88	1.02	0.0346	0.040
b	0.35	0.50	0.014	0.020
c	0.085	0.18	0.003	0.007
D	2.80	3.04	0.110	0.120
E	2.10	2.64	0.083	0.104
E ₁	1.20	1.40	0.047	0.055
e	0.95 BSC		0.0374 Ref	
e ₁	1.90 BSC		0.0748 Ref	
L	0.40	0.60	0.016	0.024
L ₁	0.64 Ref		0.025 Ref	
S	0.50 Ref		0.020 Ref	
q	3°	8°	3°	8°
ECN: S-03946-Rev. K, 09-Jul-01 DWG: 5479				

RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads
Dimensions in Inches/(mm)

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